



2N5551

NPN SILICON TRANSISTOR

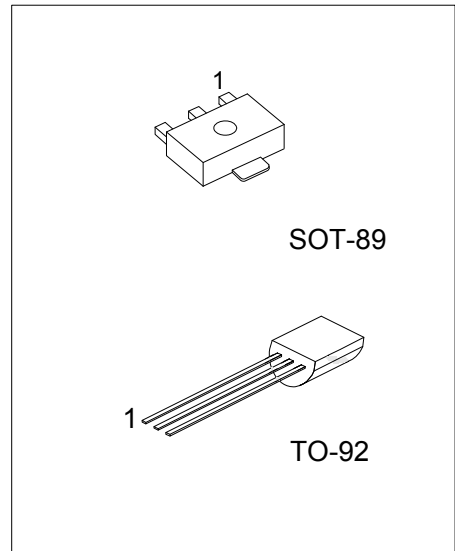
HIGH VOLTAGE SWITCHING TRANSISTOR

FEATURES

- * High collector-emitter voltage:
 $V_{CEO}=160V$
- * High current gain

APPLICATIONS

- * Telephone switching circuit
- * Amplifier



ORDERING INFORMATION

Ordering Number			Package	Pin Assignment			Packing
Normal	Lead Free Plating	Halogen Free		1	2	3	
2N5551-x-AB3-R	2N5551L-x-AB3-R	2N5551G-x-AB3-R	SOT-89	B	C	E	Tape Reel
2N5551-x-T92-B	2N5551L-x-T92-B	2N5551G-x-T92-B	TO-92	E	B	C	Tape Box
2N5551-x-T92-K	2N5551L-x-T92-K	2N5551G-x-T92-K	TO-92	E	B	C	Bulk

2N5551L-x-AB3-R	(1)Packing Type	(1) B: Tape Box, K: Bulk, R: Tape Reel
	(2)Package Type	(2) T92: TO-92, AB3: SOT-89
	(3)Rank	(3) x: refer to Classification of h_{FE}
	(4)Lead Plating	(4) L: Lead Free Plating, Blank: Pb/Sn, G: Halogen Free

■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Collector-Base Voltage	V_{CBO}	180	V
Collector-Emitter Voltage	V_{CEO}	160	V
Emitter-Base Voltage	V_{EBO}	6	V
Collector Dissipation	TO-92	625	mW
Collector Dissipation	SOT-89		
Collector Current	I_C	600	mA
Junction Temperature	T_J	+150	°C
Storage Temperature	T_{STG}	-55 ~ +150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS (Ta=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	BV_{CBO}	$I_C=100\mu A, I_E=0$	180			V
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_C=1mA, I_B=0$	160			V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_E=10\mu A, I_C=0$	6			V
Collector Cut-off Current	I_{CBO}	$V_{CB}=120V, I_E=0$			50	nA
Emitter Cut-off Current	I_{EBO}	$V_{BE}=4V, I_C=0$			50	nA
DC Current Gain(Note)	h_{FE1}	$V_{CE}=5V, I_C=1mA$	80	160	400	
	h_{FE2}	$V_{CE}=5V, I_C=10mA$	80			
	h_{FE3}	$V_{CE}=5V, I_C=50mA$	80			
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	$I_C=10mA, I_B=1mA$ $I_C=50mA, I_B=5mA$			0.15 0.2	V
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	$I_C=10mA, I_B=1mA$ $I_C=50mA, I_B=5mA$			1 1	V
Current Gain Bandwidth Product	f_T	$V_{CE}=10V, I_C=10mA, f=100MHz$	100		300	MHz
Output Capacitance	C_{ob}	$V_{CB}=10V, I_E=0, f=1MHz$			6.0	pF
Noise Figure	NF	$I_C=0.25mA, V_{CE}=5V$ $R_S=1k\Omega, f=10Hz \sim 15.7kHz$			8	dB

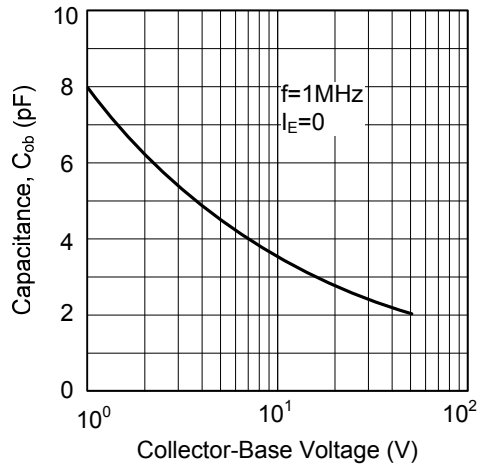
Note: Pulse test: PW<300μs, Duty cycle<2%

■ CLASSIFICATION OF h_{FE}

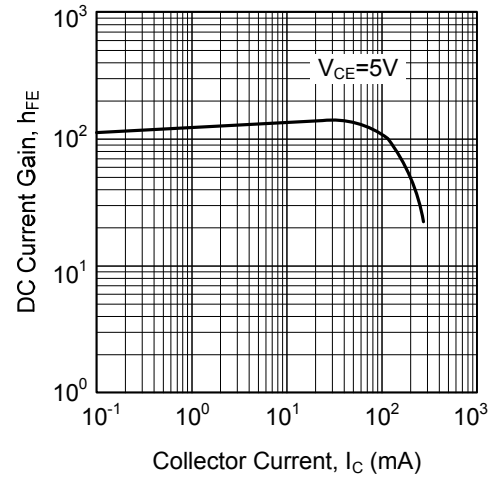
RANK	A	B	C
RANGE	80-170	150-240	200-400

■ TYPICAL CHARACTERISTICS

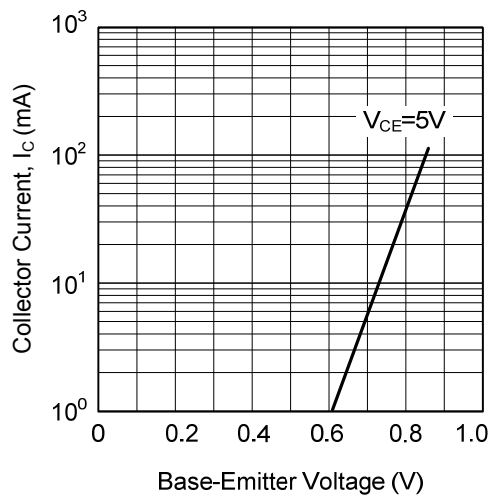
Collector Output Capacitance



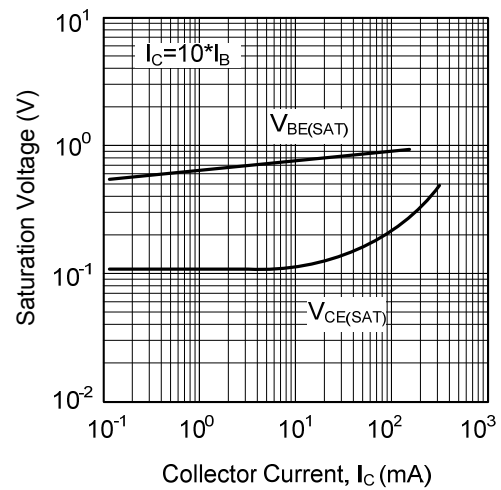
DC Current Gain



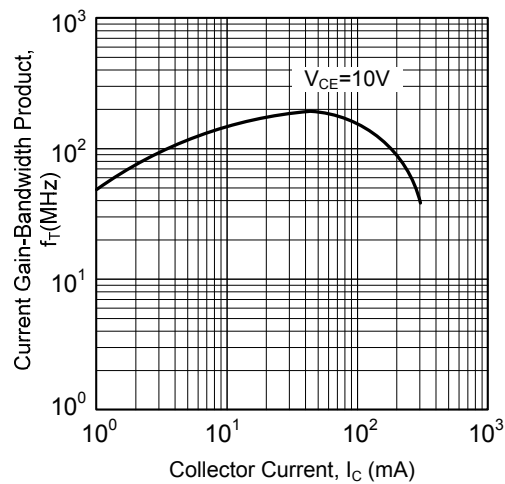
Base-Emitter on Voltage



Saturation Voltage



Current Gain-Bandwidth Product



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